

LISTING OF THE CLAIMS

The following is a listing of claims pending in the application.

- 1-7. **(Cancelled)**
8. **(Previously Presented)** A long wavelength vertical cavity surface emitting laser comprising:
 - a substrate;
 - a first mirror proximate said substrate and having a plurality of layers including at least one pair of layers having a non-oxidized AlGaInAs layer and an oxidized layer, wherein the oxidized layer comprises at least one of oxidized InGaAsP, InAlAs, InAlGaAs, AlAsSb, AlGaAsSb, AlGaPSb or AlPSb;
 - a cavity proximate to said first mirror;
 - a second mirror proximate to said cavity, said second mirror comprising a partially oxidized layer for confining current; and
 - at least two contacts configured to cause current to flow through at least a portion of the vertical cavity surface emitting laser.
9. **(Original)** The laser of claim 8, wherein said first mirror is proximate to an InP substrate.
10. **(Previously Presented)** The laser of claim 12, wherein the at least one quantum well is configured to emit energy at a wavelength greater than 1200 nm.
11. **(Previously Presented)** The laser of claim 8, wherein said second mirror comprises a plurality of layers having at least one InP layer.
12. **(Previously Presented)** The laser of claim 8, wherein said cavity has at least one quantum well.
13. **(Cancelled)**

14. **(Previously Presented)** The laser of claim 8, further comprising:
 a first electrical contact on said second mirror; and
 a second electrical contact on the substrate.

15. **(Previously Presented)** The laser of claim 8, further comprising:
 an intra-cavity contact layer situated between said first mirror and said cavity;
 a first contact on said second mirror; and
 a second contact on said intra-cavity contact layer.

- 16-35. **(Cancelled)**

36. **(Previously Presented)** The laser of claim 8, wherein the plurality of layers of the first
mirror has six or fewer pairs of layers.

37. **(Cancelled)**